

# **ABSTRACT OF THE DISCLOSURE**

A method for fabricating a semiconductor a  
semiconductor device having a stacked-gate structure. A  
polysilicon layer is formed overlying a substrate, which is  
5 insulated from the substrate by a dielectric layer. A  
metal-flash layer is formed overlying the polysilicon layer,  
and then a tungsten nitride layer is formed overlying the  
titanium layer. The tungsten nitride layer is annealed  
using nitrogen and hydrogen gases. A tungsten layer and a  
10 cap layer are successively formed overlying the tungsten  
nitride layer.